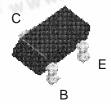


FSB660 / FSB660A



SuperSOT[™]-3 (SOT-23)

PNP Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 2A continuous.

Absolute Maximum Ratings* T_{A = 25°C unless otherwise noted}

Symbol	Parameter	FSB660/FSB660A	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	2	А
T _{J,} T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_{A = 25°C unless otherwise noted}

Symbol	Characteristic	Max	Units
392 14	71-	FSB660/FSB660A	
PD	Total Device Dissipation	500	mW
R _θ JA	Thermal Resistance, Junction to Ambient	250	°C/W

Electric	al Characteristics T _{A = 25°C unless otherwise}	e noted			
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA	60		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V		100	nA
		V _{CB} = 30 V, T _A =100°C		10	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
ON CHAR	RACTERISTICS*		1		
h _{FE}	DC Current Gain	I _C = 100 mA, V _{CE} = 2 V	70		-
		I _C =500mA, V _{CE} =2V FSB660	100	300	
		FSB660A	250	550	
		$I_C = 1 A, V_{CE} = 2 V$	80		
		$I_C = 2 A, V_{CE} = 2 V$	40		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		300	mV
-(,		I _C = 2 A, I _B =200 mA FSB660		350	
		FSB660A		300	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V

 $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{MHz}$

 $I_C = 100 \text{ mA}, V_{CE} = 5 \text{ V}, f=100 \text{MHz}$

*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Output Capacitance

Transition Frequency

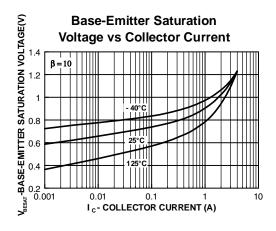
 $\mathsf{C}_{\mathsf{obo}}$

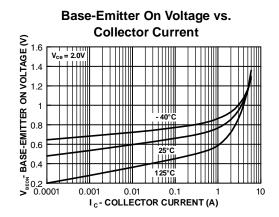
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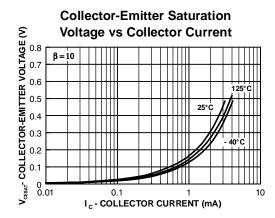
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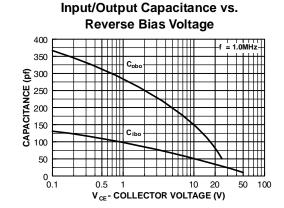
рF

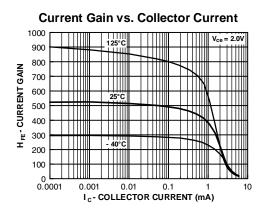
Typical Characteristics

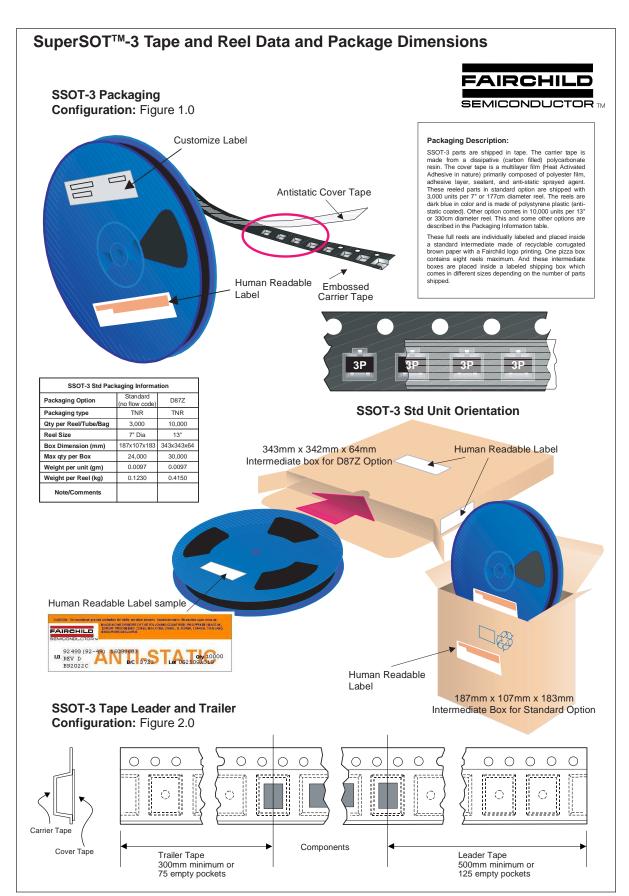








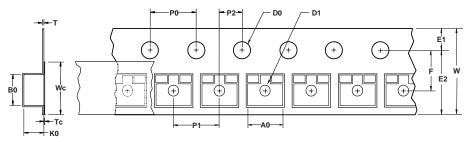


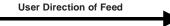


SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



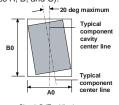


					Di	mension	s are in r	nillimetei	r					
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



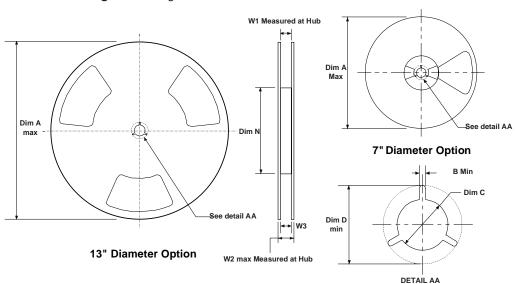
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

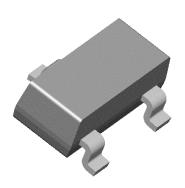
SSOT-3 Reel Configuration: Figure 4.0

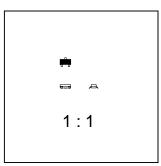


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

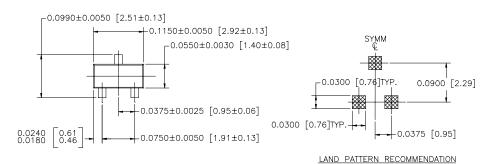
SuperSOT™-3 (FS PKG Code 32)

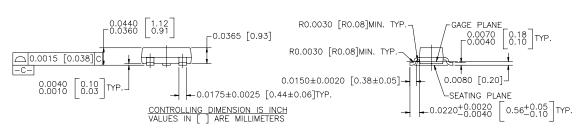




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097





NOTES : UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.

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FAST $^{\otimes}$ Quiet SeriesTM
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SuperSOT™-6

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

SuperSOT™-8

SyncFET™

TinyLogic[™]

UHC™ VCX™

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition				
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Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.				